Amendments to the Claims:

1. (Currently amended) A structure, comprising:

an external terminal;

a reference terminal;

a first transistor formed on a substrate, the first transistor having a current path electrically connected ~~coupled~~ between the external terminal and the reference terminal;

a second transistor having a current path electrically connected ~~coupled~~ between the external terminal and the substrate; and

a third transistor having a current path electrically connected ~~coupled~~ between the substrate and the reference terminal, wherein the current paths of the second and third transistors are in parallel with the current path of the first transistor.

2. (Original) A structure as in claim 1, further comprising:

a first resistor coupled between the external terminal and the current path of the second transistor; and

a second resistor coupled between the current path of the third transistor and the reference terminal.

3. (Original) A structure as in claim 1, wherein the substrate is a first lightly doped region having a first conductivity type.

4. (Original) A structure as in claim 3, further comprising:

a first heavily doped region having a second conductivity type and underlying the substrate and the first transistor; and

a second lightly doped region having the second conductivity type, the second lightly doped region formed at a face of the substrate and extending to the first heavily doped region.

5. (Original) A structure as in claim 4, further comprising:

a first diode coupled between the external terminal and the second lightly doped region; and

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a second diode coupled between the reference terminal and the second lightly doped region.

6. (Currently amended) A structure as in claim 1, wherein the first transistor further comprises a control terminal electrically connected ~~coupled~~ to the substrate.

7. (Original) A structure as in claim 6, further comprising:

a first resistor coupled between the external terminal and the current path of the second transistor; and

a second resistor coupled between the current path of the third transistor and the reference terminal.

8. (Original) A structure as in claim 7, wherein the substrate is a first lightly doped region having a first conductivity type, the structure further comprising:

a first heavily doped region having a second conductivity type and underlying the substrate and the first transistor; and

a second lightly doped region having the second conductivity type, the second lightly doped region formed at a face of the substrate and extending to the first heavily doped region.

9. (Original) A structure as in claim 8, further comprising:

a first diode having a first terminal coupled to the second lightly doped region and having a second terminal coupled between the first resistor and the current path of the second transistor; and

a second diode having a first terminal coupled to the second lightly doped region and having a second terminal coupled between the second resistor and the current path of the third transistor.

10. (Original) A structure as in claim 9, further comprising:

an isolation circuit connected to the external terminal; and

a protected circuit electrically connected to the isolation circuit.

11. (Original) A structure as in claim 1, further comprising a protected circuit electrically connected to the external terminal.

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12. (Currently amended) A structure as in claim 1, wherein the first transistor is an MOS transistor having a control gate electrically connected ~~coupled~~ to the substrate.

13. (Currently amended) A structure as in claim 1, wherein the first transistor is a bipolar transistor having a base terminal electrically connected ~~coupled~~ to the substrate.

Claims 14-45 (cancelled)

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